

## N-Channel Enhancement Mode Power MOSFET

### Description

The PT HGĒ Ö uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. It can be used in Automotive applications and a wide variety of other applications.

### General Features

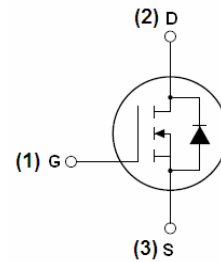
- $V_{DSS} = 75V, I_D = 210A$   
 $R_{DS(ON)} < 4m\Omega @ V_{GS} = 10V$
- Good stability and uniformity with high  $E_{AS}$
- Special process technology for high ESD capability
- High density cell design for ultra low  $R_{dson}$
- Fully characterized avalanche voltage and current
- Excellent package for good heat dissipation

### Application

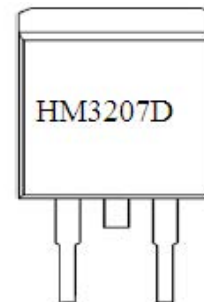
- Automotive applications
- Hard switched and high frequency circuits
- Uninterruptible power supply

**100% UIS TESTED!**

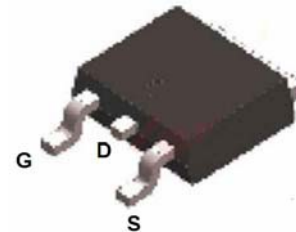
**100%  $\Delta V_{ds}$  TESTED!**



Schematic diagram



Marking and pin assignment



TO-263-2L top view

### Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
PT HGĒ Ö	PT HGĒ Ö	TO-263-2L	-	-	-

### Absolute Maximum Ratings ( $T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DSS}$	75	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous	$I_D$	210	A
Drain Current-Continuous( $T_C = 100^\circ C$ )	$I_D(100^\circ C)$	150	A
Pulsed Drain Current	$I_{DM}$	840	A
Maximum Power Dissipation	$P_D$	330	W
Derating factor		2.2	W/ $^\circ C$
Single pulse avalanche energy (Note 4)	$E_{AS}$	2200	mJ
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 175	$^\circ C$

### Thermal Characteristic

Thermal Resistance, Junction-to-Case (Note 1)	$R_{\theta JC}$	0.455	$^{\circ}C/W$
---	-----------------	-------	---------------

### Electrical Characteristics (TA=25 $^{\circ}C$ unless otherwise noted)

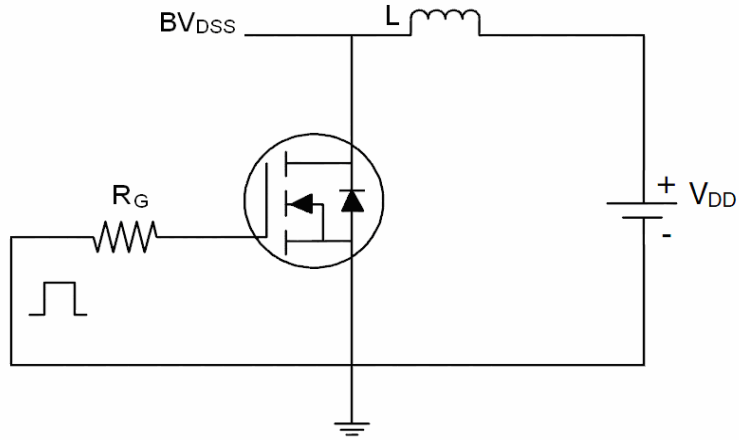
Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	75			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=75V, V_{GS}=0V$			1	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$			$\pm 200$	nA
<b>On Characteristics</b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2	3	4	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=40A$		3	4	m $\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS}=25V, I_D=40A$	100	165		S
<b>Dynamic Characteristics</b>						
Input Capacitance	$C_{iss}$	$V_{DS}=25V, V_{GS}=0V,$ $F=1.0MHz$		11000		PF
Output Capacitance	$C_{oss}$			914		PF
Reverse Transfer Capacitance	$C_{rss}$			695		PF
<b>Switching Characteristics</b>						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=30V, I_D=2A, R_L=15\Omega$ $V_{GS}=10V, R_G=2.5\Omega$		23		nS
Turn-on Rise Time	$t_r$			190		nS
Turn-Off Delay Time	$t_{d(off)}$			130		nS
Turn-Off Fall Time	$t_f$			120		nS
Total Gate Charge	$Q_g$	$I_D=30A, V_{DD}=30V, V_{GS}=10V$	-	250		nC
Gate-Source Charge	$Q_{gs}$		-	48		nC
Gate-Drain Charge	$Q_{gd}$		-	98		nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage	$V_{SD}$	$V_{GS}=0V, I_S=40A$			1.2	V
Reverse Recovery Time	$t_{rr}$	$T_J = 25^{\circ}C, I_F = 40A$ $di/dt = 100A/\mu s$ (Note2)		48		nS
Reverse Recovery Charge	$Q_{rr}$			78		nC
Forward Turn-On Time	$t_{on}$	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

### Notes:

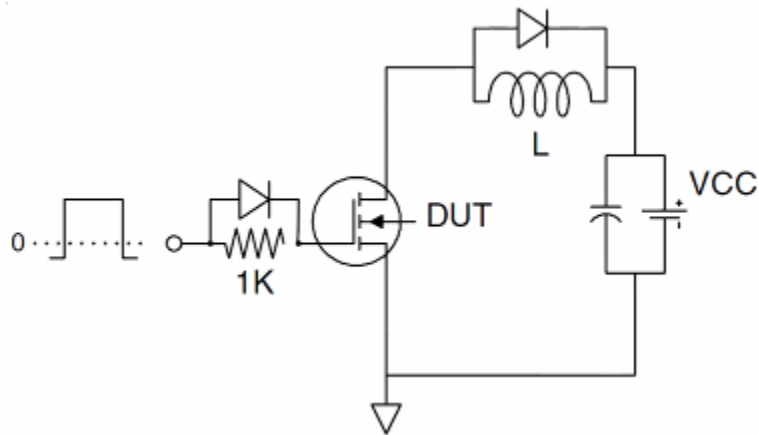
1. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
2. Pulse Test: Pulse Width  $\leq 400\mu s$ , Duty Cycle  $\leq 2\%$ .
3. EAS condition:  $T_J=25^{\circ}C, V_{DD}=37.5V, V_G=10V, L=0.5mH, R_g=25\Omega, I_{AS}=37A$

**Test circuit**

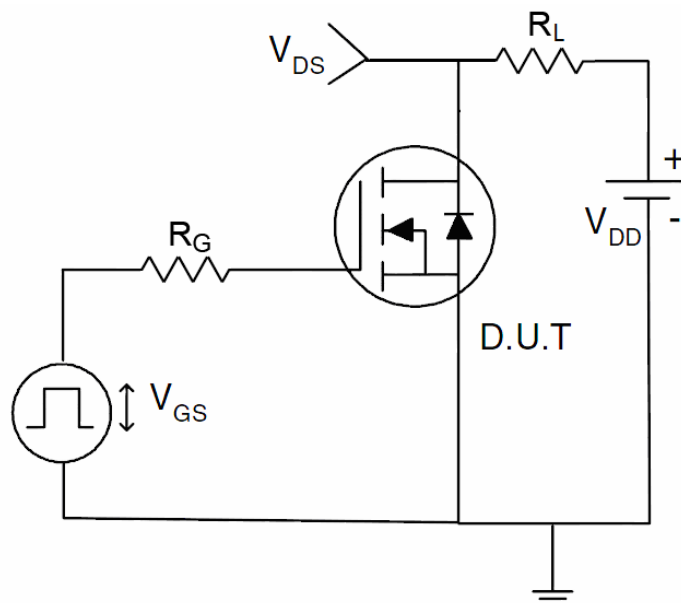
**1)  $E_{AS}$  test Circuit**



**2) Gate charge test Circuit**



**3) Switch Time Test Circuit**



Typical Electrical and Thermal Characteristics

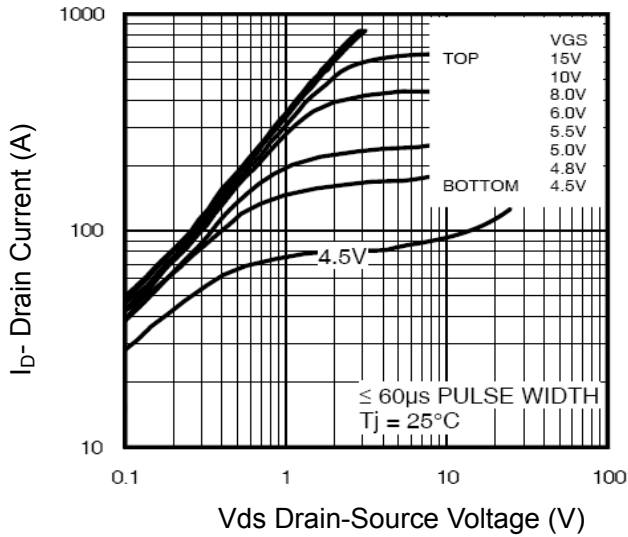


Figure 1 Output Characteristics

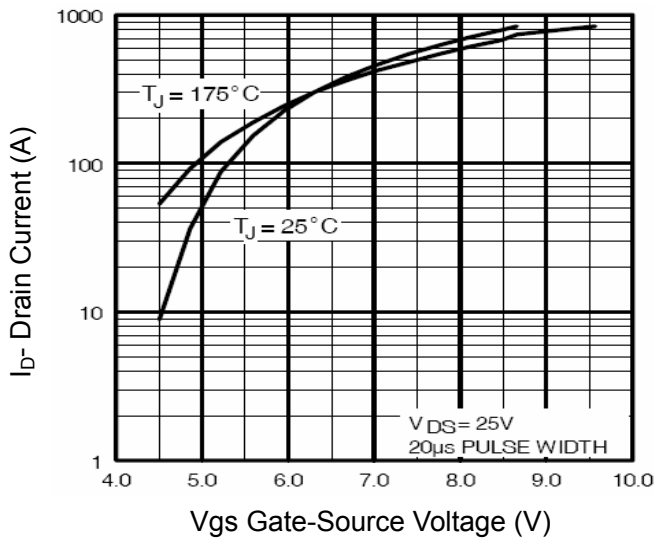


Figure 2 Transfer Characteristics

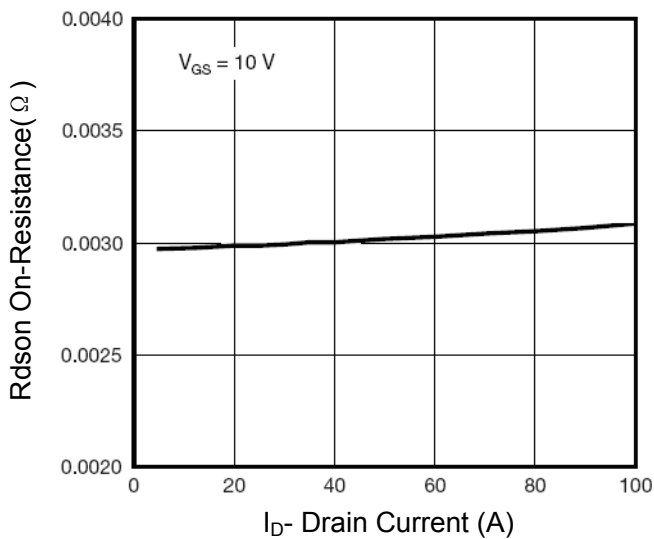


Figure 3 Rdson- Drain Current

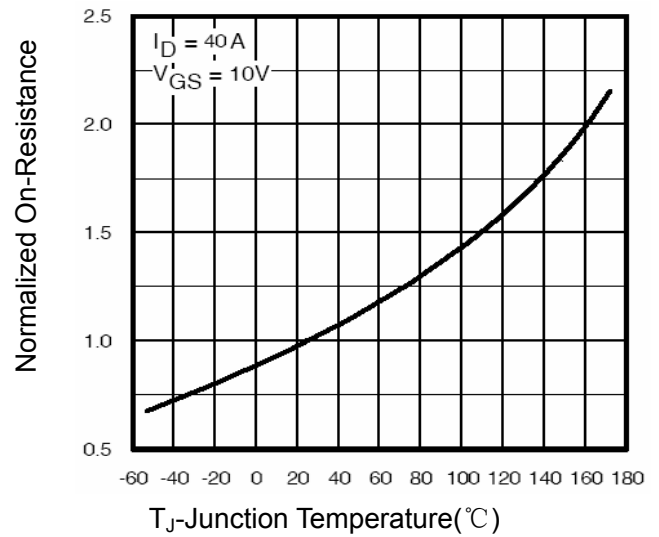


Figure 4 Rdson-Junction Temperature

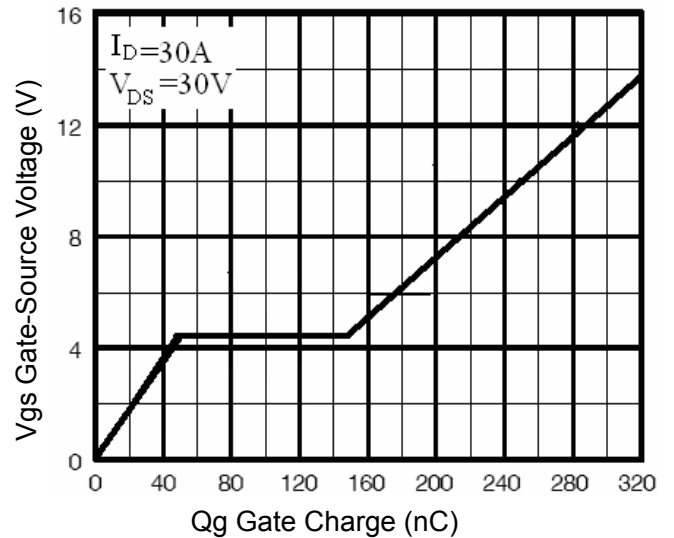


Figure 5 Gate Charge

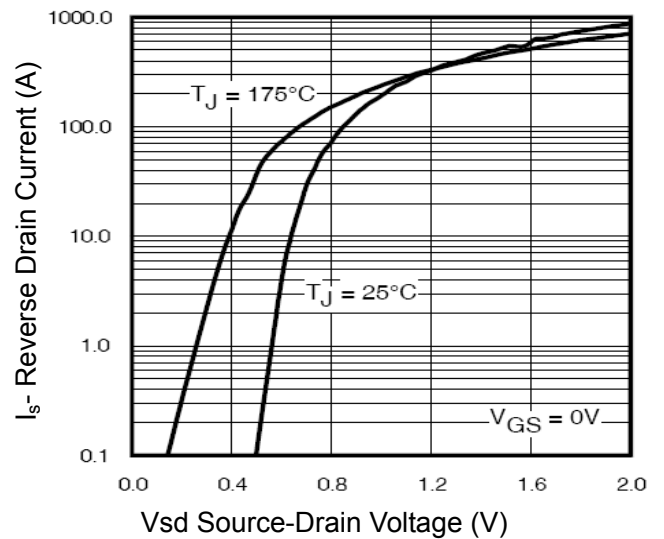


Figure 6 Source- Drain Diode Forward

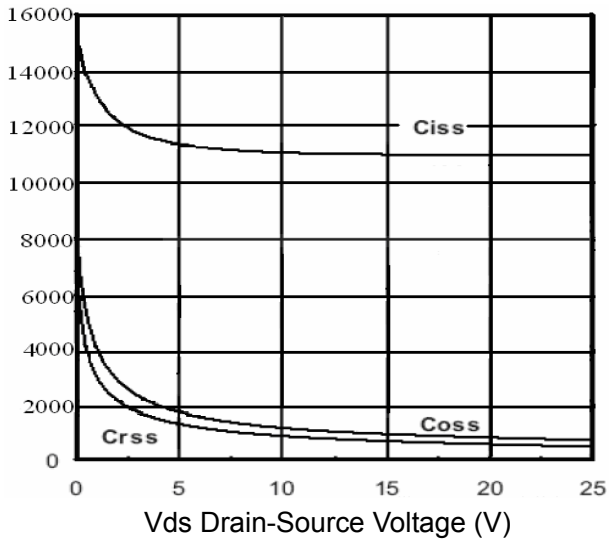


Figure 7 Capacitance vs Vds

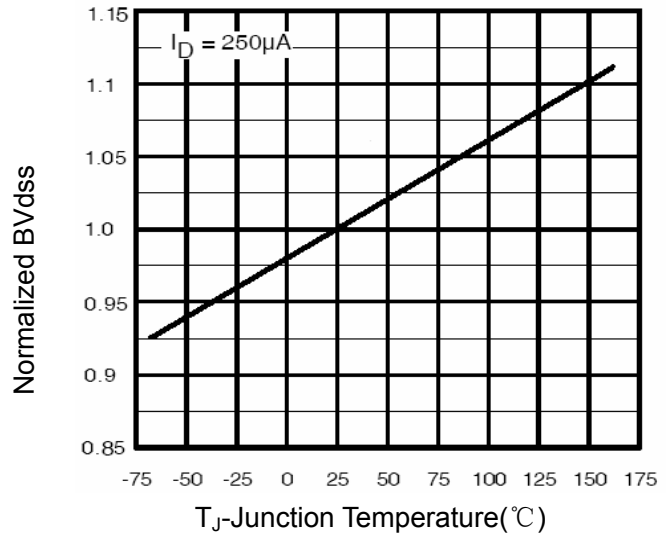


Figure 9  $BV_{DSS}$  vs Junction Temperature

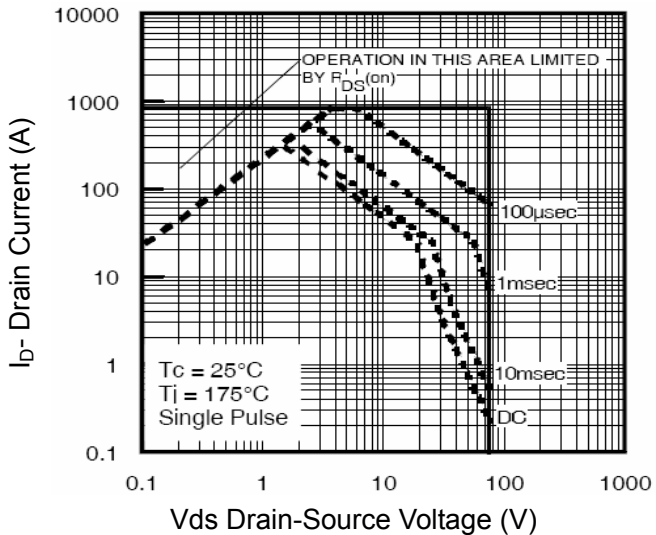


Figure 8 Safe Operation Area

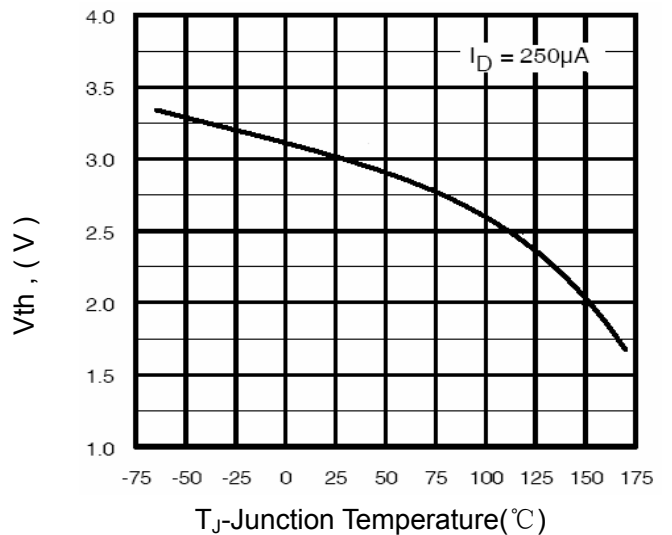


Figure 10  $V_{GS(th)}$  vs Junction Temperature

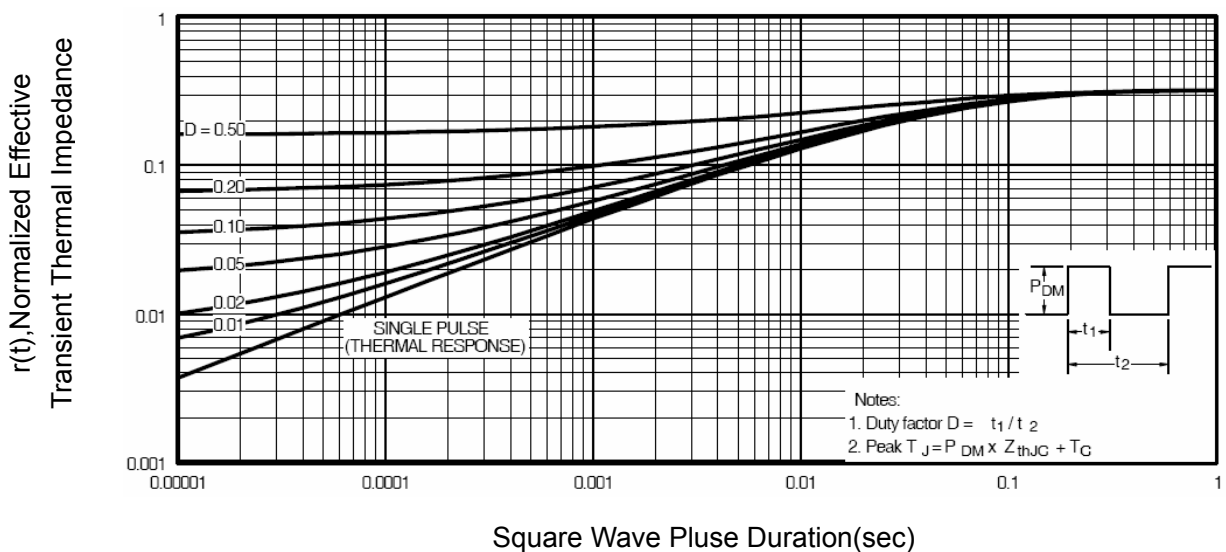
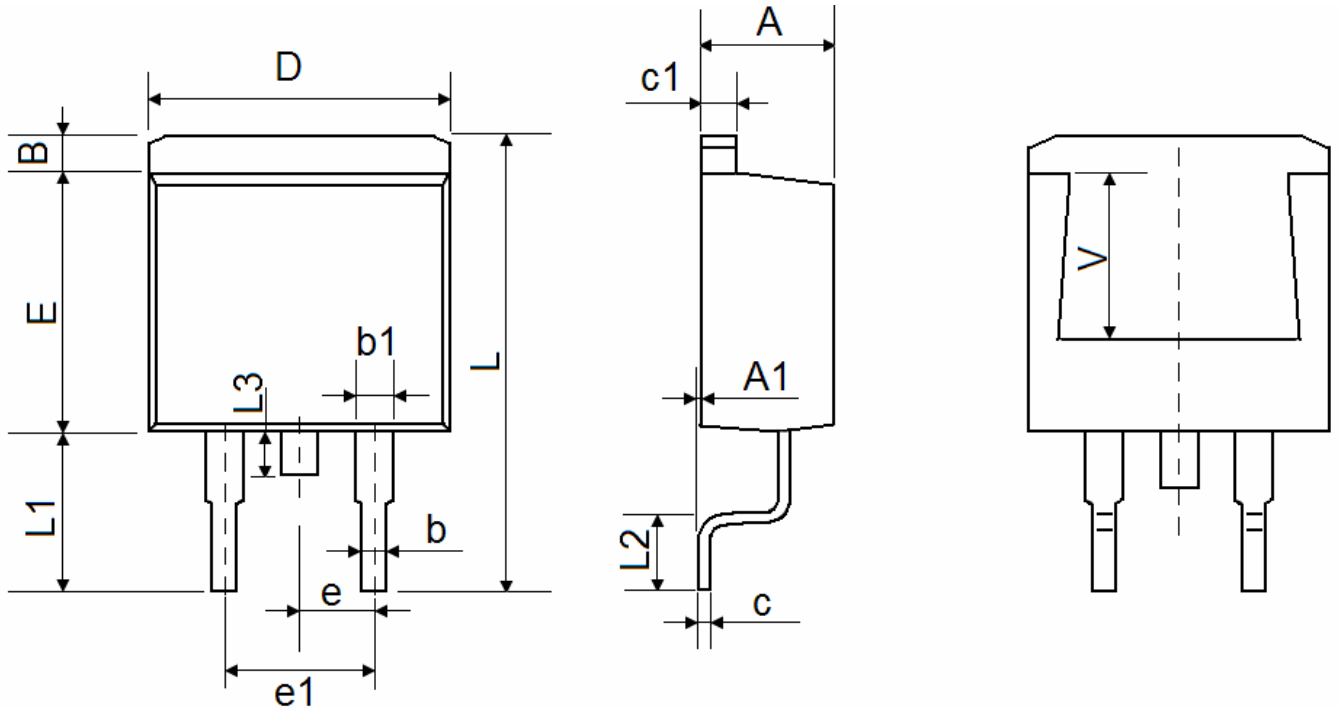


Figure 11 Normalized Maximum Transient Thermal Impedance

## TO-263-2L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.470	4.670	0.176	0.184
A1	0.000	0.150	0.000	0.006
B	1.170	1.370	0.046	0.054
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.310	0.530	0.012	0.021
c1	1.170	1.370	0.046	0.054
D	10.010	10.310	0.394	0.406
E	8.500	8.900	0.335	0.350
e	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
L	15.050	15.450	0.593	0.608
L1	5.080	5.480	0.200	0.216
L2	2.340	2.740	0.092	0.108
L3	1.300	1.700	0.051	0.067
V	5.600 REF		0.220 REF	